# N-Channel 20-V (D-S) MOSFET

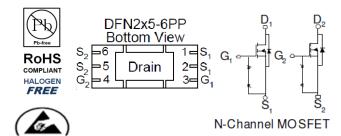
### **Key Features:**

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- · Fast switching speed

## **Typical Applications:**

- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits
- · Typical ESD protection, HBM Class 1

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	In (A)		
20	9.5 @ V <sub>GS</sub> = 4.5V	16		
20	13 @ V <sub>GS</sub> = 2.5V	13		



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 ℃ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage	rain-Source Voltage		20	V		
Gate-Source Voltage		$V_{GS}$	±8	V		
Continuous Dunin Comment <sup>a</sup>	T <sub>A</sub> =25℃	ı	16	А		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70 °C	ID	11.3			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	85			
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	5.2	Α		
Danier Discipation a	T <sub>A</sub> =25℃	$P_D$	3.5	w		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70 ℃	ı D	1.8	V V		
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	℃		

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	36	°C/W		
IMAXIIIUIII JUIICIIOII-IO-AIIIDIEIII	Steady State	ιθJA	76	C/VV		

### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

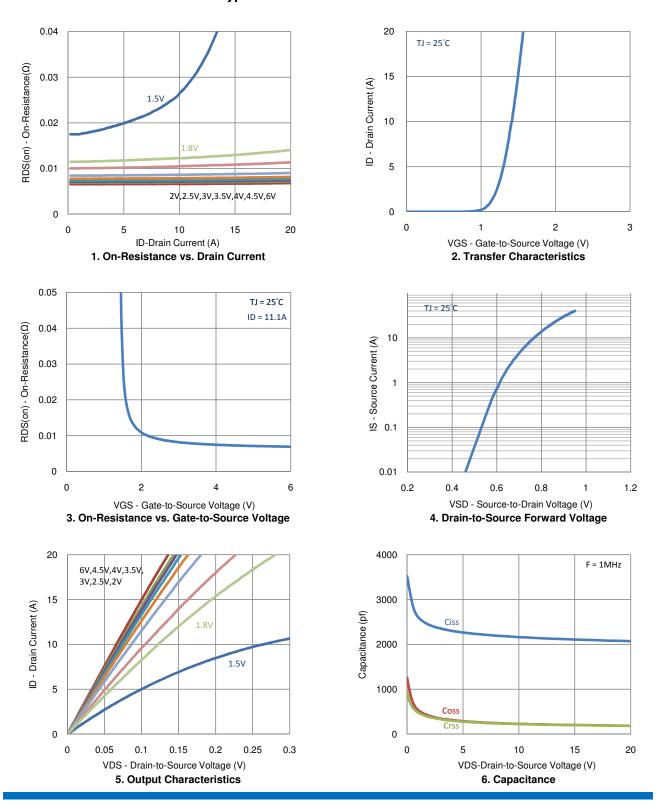
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero date Voltage Brain Gurrent	טטי	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$		25		uA	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	25			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		8	9.5		
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 3.8 \text{ V}, I_D = 10.4 \text{ A}^b$		9	11	mΩ	
Dialii-Source Oil-nesistance	r <sub>DS(on)</sub>	$V_{GS} = 3.1 \text{ V}, I_D = 9.7 \text{ A}^b$		10	12		
		$V_{GS} = 2.5 \text{ V}, I_D = 9 \text{ A}$		11	13		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 11 \text{ A}$		16		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.67		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		19			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 11 \text{ A}$		3.4		nC	
Gate-Drain Charge	$Q_{gd}$	יש די		4.5		]	
Turn-On Delay Time	$t_{d(on)}$			15			
Rise Time	t <sub>r</sub>	$V_{DS}=10~V,~R_L=1~\Omega,~I_D=11~A,$		52		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		82			
Fall Time	$t_f$			35			
Input Capacitance	$C_{iss}$			2109			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		204		pF	
Reverse Transfer Capacitance	$C_{rss}$			201			

### Notes

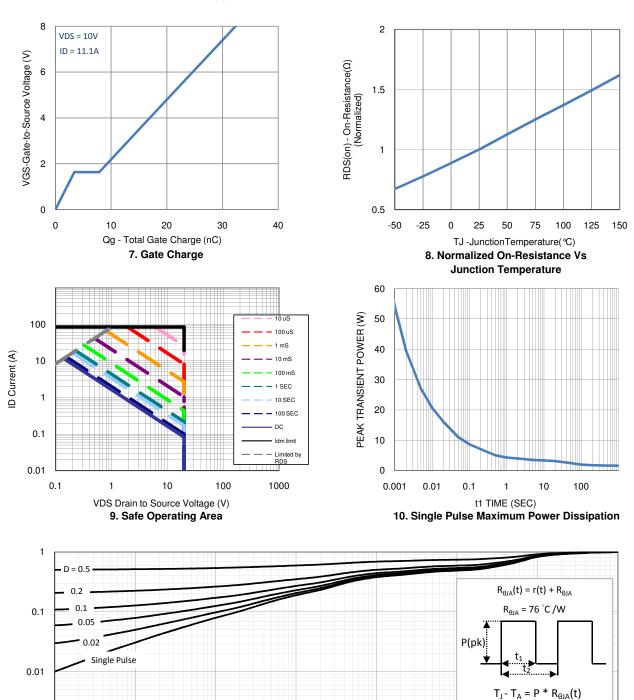
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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## **Typical Electrical Characteristics**



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t1 TIME (sec)

11. Normalized Thermal Transient Junction to Ambient

0.1

0.001

0.0001

0.001

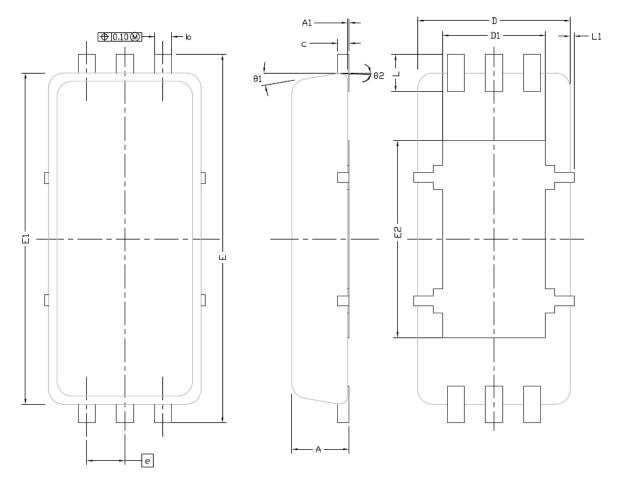
0.01

Duty Cycle,  $D = t_1 / t_2$ 

100

10

# **Package Information**



	MILLIMETERS			INCHES			
DIM.	MIN	NDM	MAX	MIN	NOM	MAX	
Α	0.70	0.75	0.80	0.028	0.030	0.0315	
A1	0,00		0.05	0,000		0,002	
ю	0.20	0.225	0.30	0.008	0.009	0.012	
С	0.10	0.152	0.20	0.004	0.005	0.008	
D	â	2.00 BSC			0.079 BSC		
D1	1,30	1.35	1.55	0.051	0.053	0.061	
E	5.00 BSC			0.197 BSC			
E1	4	1.50 BS	С	0.	177 BSC		
E3	2.60	2.67	2.95	0.102	0.105	0.116	
е	0	0.50 BSC			0.020 BSC		
L	0.40	0.50	0.600	0.016	0.0197	0.0236	
L1	0		0,100	0		0,004	
91	0°	10°	12°	0.	10°	15,	
62	3, 320			3. BZC			